

• General Description

The 120N04KG uses SGT and design to provide excellent $R_{ds(on)}$ with low gate charge. It can be used in a wide variety of applications.

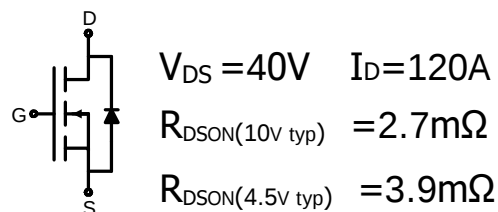
• Features

High density cell design for ultra low $R_{ds(on)}$
Fully characterized avalanche voltage and current
Good stability and uniformity with high EAS
Excellent package for good heat dissipation

• Application

MB/VGA Vcore
SMPS 2nd Synchronous Rectifier
POL application
BLDC Motor driver

• Product Summary



TO-252

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@T_C=25^\circ C}$	120	A
	$I_{D@T_C=75^\circ C}$	84	A
	$I_{D@T_C=100^\circ C}$	72	A
Pulsed Drain Current ①	I_{DM}	360	A
Total Power Dissipation	$P_{D@T_C=25^\circ C}$	125	W
Total Power Dissipation	$P_{D@T_A=25^\circ C}$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Single Pulse Avalanche Energy	E _{AS}	100			mJ	
Avalanche Current	I _{AS} I _{AR}	30			A	
●Thermal resistance						
Parameter	Symbol	Min.	Typ.	Max.	Unit	
Thermal resistance, junction - case	R _{thJC}	-	-	3.5	° C/W	
Thermal resistance, junction - ambient	R _{thJA}	-	-	58	° C/W	
Soldering temperature, wave soldering for 8s	T _{sold}	-	-	265	° C	
●Electronic Characteristics						
Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	40			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.0	1.6	2.1	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V ,V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A		2.7	3.5	mΩ
		V _{GS} = 4.5V, I _D = 20A		3.9	5.0	mΩ
Forward Transconductance	g _{FS}	V _{DS} =15V, I _D =20A		15		S
Source-drain voltage	V _{SD}	Is=20A			1.20	V
●Electronic Characteristics						
Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	Ciss	Vds=25V,Vgs=0V f = 1MHz	-	2400	-	pF
Output capacitance	Coss		-	430.0	-	
Reverse transfer capacitance	Crss		-	410.0	-	
●Gate Charge characteristics(T _a = 25°C)						
Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Risistance	R _g	f = 1MHz		1.1		Ω
Total gate charge	Qg	V _{DD} = 20V I _D = 30A V _{GS} = 10V	-	57.8	-	nC
Gate - Source charge	Qgs		-	10.7	-	
Gate - Drain charge	Qgd		-	17.6	-	
Turn-ON Delay time	t _{D(on)}	V _{GS} =10V ,V _{DS} =20V R _G =1.1Ω, I=30A		17.0		ns
Turn-ON Rise time	t _r			9.8		ns
Turn-Off Delay time	t _{D(off)}			54		ns
Turn-Off Fall time	t _f			30		ns

Fig.1 Power Dissipation

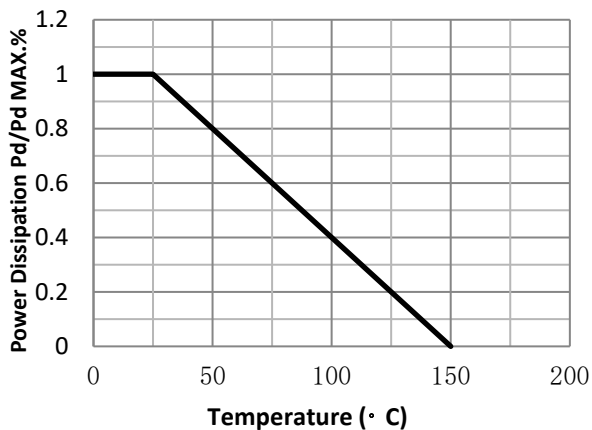


Fig.2 Typical output Characteristics

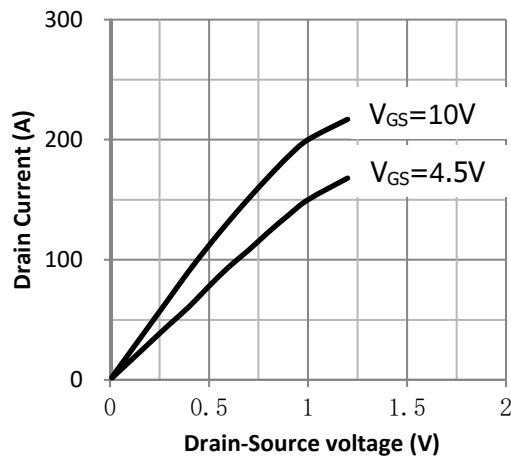


Fig.3 Threshold Voltage V.S Junction Temperature

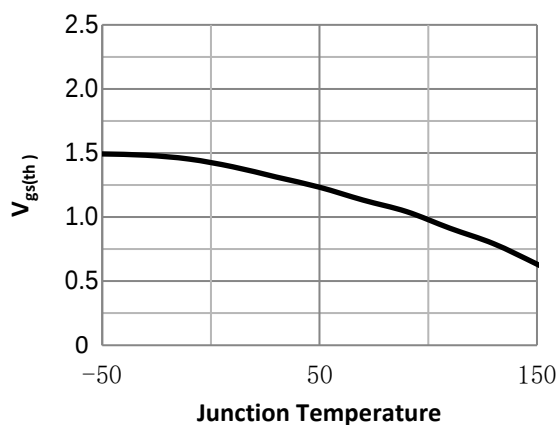


Fig.4 Resistance V.S Drain Current

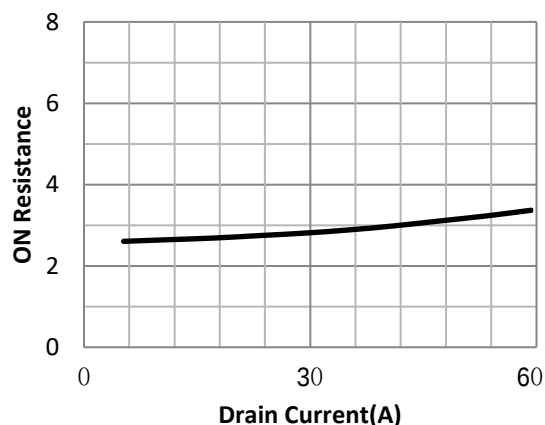


Fig.5 On-Resistance VS Drain Current

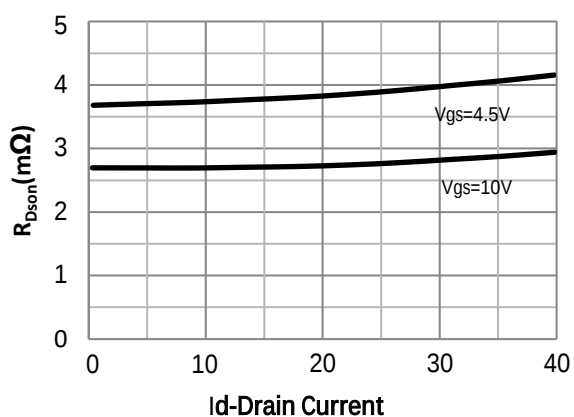


Fig.6 On-Resistance V.S Junction Temperature

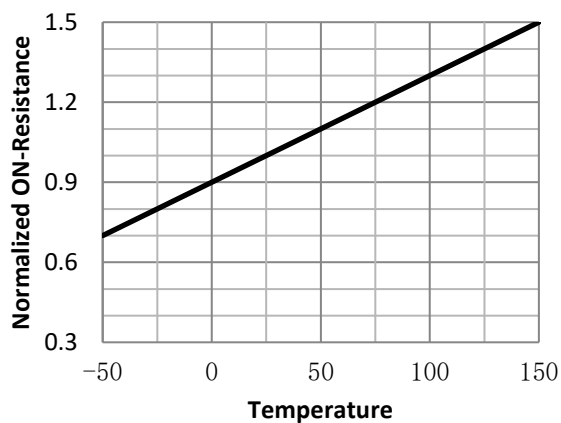


Fig.7 Switching Time Measurement Circuit

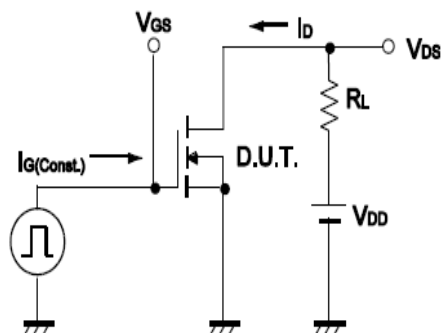


Fig.8 Gate Charge Waveform

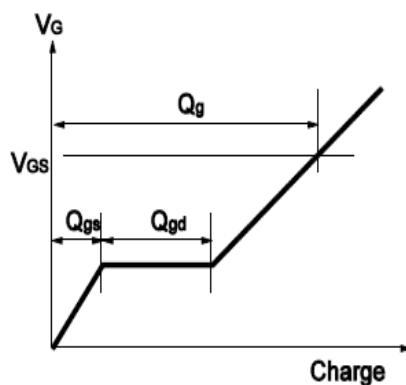


Fig.9 Switching Time Measurement Circuit

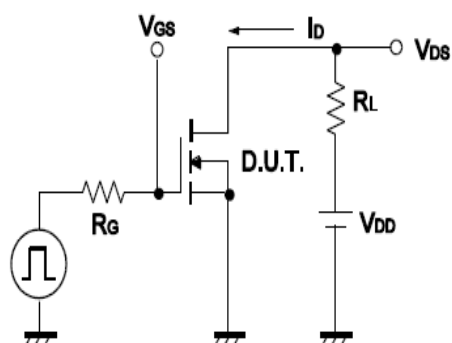


Fig.10 Gate Charge Waveform

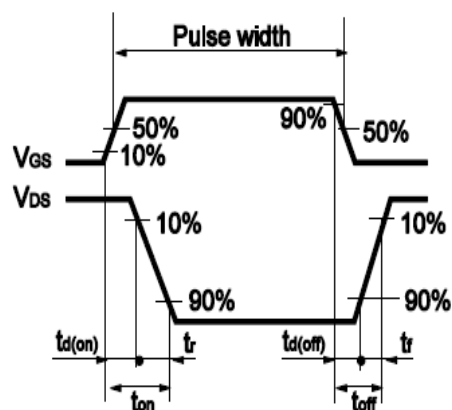


Fig.11 Avalanche Measurement Circuit

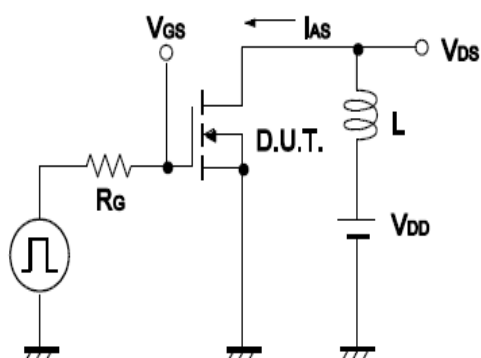
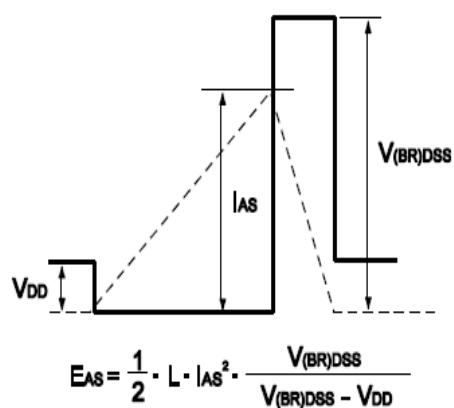
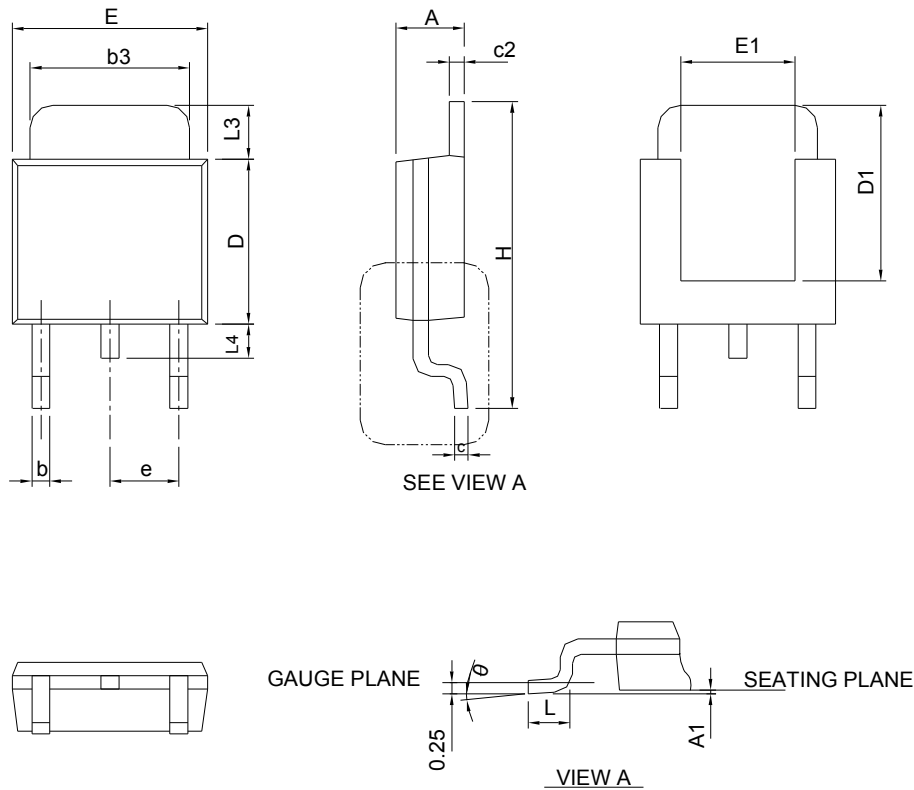


Fig.12 Avalanche Waveform



Package Information

TO-252



	TO-252			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1		0.13		0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4		1.02		0.040
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN

